

**LISTING OF CLAIMS**

This listing of claims replaces all prior versions and listings of claims in the patent application.

Claim 1 (original): A pressure sensor comprising a silicon structure having a conductive diaphragm, the silicon structure being bonded on a substrate, which comprises an electrode covered by a dielectric film, so that the diaphragm and the electrode are facing each other and there is a gap between the diaphragm and the dielectric film, the pressure sensor measuring a pressure applied thereto by detecting capacitance according to the area of a contact face of the diaphragm which touches the dielectric film when the pressure is applied;

the concentration of an impurity at the top face of the diaphragm being equal to or greater than  $1\times10^{19}$  cm<sup>-3</sup> and less than  $9\times10^{19}$  cm<sup>-3</sup>.

Claim 2 (withdrawn): A manufacturing method for a pressure sensor comprising a silicon structure having a conductive diaphragm, the silicon structure being bonded on a substrate, which comprises an electrode covered by a dielectric film, so that the diaphragm and the electrode are facing each other and there is a gap between the diaphragm and the dielectric film, the pressure sensor measuring a pressure applied thereto by detecting capacitance according to the area of a contact face of the diaphragm which touches the dielectric film when the pressure is applied, the method comprising a step of

manufacturing the silicon structure by doping the top face of the silicon with an impurity at high concentration, and providing the diaphragm by etching so that the concentration of the impurity at the top face is equal to or greater than  $1\times10^{19}$  cm<sup>-3</sup> and less than  $9\times10^{19}$  cm<sup>-3</sup>.

Claim 3 (withdrawn): The pressure sensor manufacturing method according to Claim 2, wherein at least one solution selected from a group comprising KOH, NaOH, ethylene diamine pyrocatechol (EDP), and tetramethyl ammonium hydroxide (TMAH) is used as the solution for etching.

Claim 4 (original): A pressure sensor comprising a silicon structure having a conductive diaphragm, provided by doping of an impurity and anisotropic etching, the silicon structure being bonded on a substrate, which comprises an electrode covered by a dielectric film, so that the diaphragm and the electrode are facing each other and there is a gap between the diaphragm and the dielectric film, the pressure sensor measuring a pressure applied thereto by detecting capacitance according to the area of a contact face of the diaphragm which touches the dielectric film when the pressure is applied;

the etch pit density on the top face of the diaphragm being equal to or less than five per  $\mu\text{m}^2$ .

Claim 5 (withdrawn): A manufacturing method for a pressure sensor comprising a silicon structure having a conductive diaphragm, provided by doping of an impurity and anisotropic etching, the silicon structure being bonded on a substrate, which comprises an electrode covered by a dielectric film, so that the diaphragm and the electrode are facing each other and there is a gap between the diaphragm and the dielectric film, the pressure sensor measuring a pressure applied thereto by detecting capacitance according to the area of a contact face of the diaphragm which touches the dielectric film when the pressure is applied; the method comprising a step of

manufacturing the silicon structure by doping the top face of the silicon with an impurity at high concentration, and etching the diaphragm so that the etch pit density on the top face of the diaphragm is equal to or less than five per  $\mu\text{m}^2$ .

Claim 6 (withdrawn): The pressure sensor manufacturing method according to Claim 5, wherein the etching is performed using KOH solution having concentration of equal to or greater than 1 weight % and less than 10 weight %, the etch pit density on the top etching face being equal to or less than one per  $\mu\text{m}^2$ .

Claim 7 (withdrawn): A pressure sensor for detecting the pressure of vehicle tires manufactured by any the methods according to Claims 2, 3, 5, and 6.

Claim 8 (previously presented): The pressure sensor of claim 1, wherein the impurity is boron.

Claim 9 (previously presented): The pressure sensor of claim 4, wherein in etch pit density on the top face of the diaphragm is equal to or less than three pits per  $\mu\text{m}^2$ .

Claim 10 (previously presented): The pressure sensor of claim 4, wherein in etch pit density on the top face of the diaphragm is equal to or less than one pit per  $\mu\text{m}^2$ .

Claim 11 (previously presented): The pressure sensor of claim 4, wherein the impurity is boron.